

RoHS Compliant Product
A suffix of "C" specifies halogen & lead-free

DESCRIPTION

The KS05UL5 provides a typical line to line capacitance of 0.3pF between I/O pins and low insertion loss up to 3GHz providing greater signal integrity making it ideally suited for HDMI applications, such as Digital TVs, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

APPLICATIONS

- TVs, monitors , audio
- Portable devices
- Notebooks, mother boards, graphic cards and ports.
- Set-top box and game consoles.

FEATURES

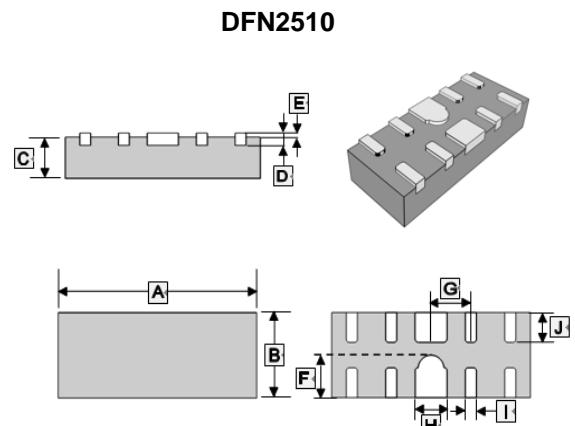
- Low capacitance: 0.3pF Typical between I/O channel
- Low leakage current
- Response time < 1ns
- Solid-state silicon avalanche technology

MARKING

.0524P

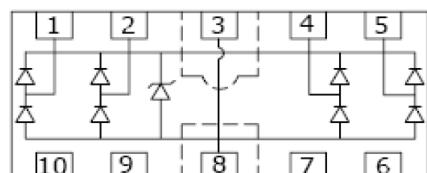
PACKAGE INFORMATION

Package	MPQ	Leader Size
DFN2510	3K	7 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.40	2.60	F	0.41	0.61
B	0.90	1.10	G	0.500	TYP.
C	0.55	TYP.	H	0.30	0.50
D	0.150	REF.	I	0.15	0.25
E	0.00	0.05	J	0.30	0.46

(Top view)



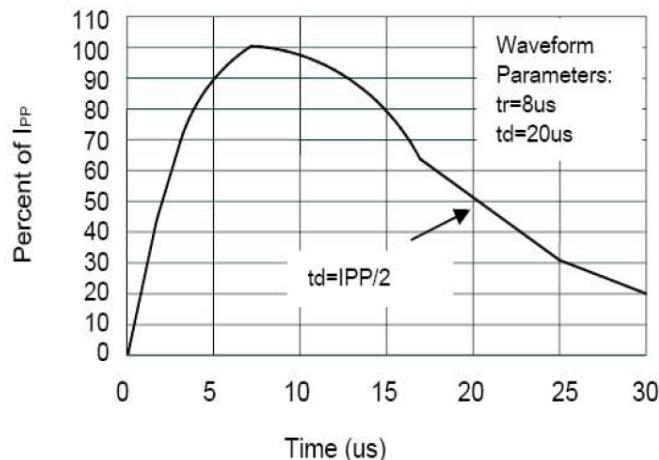
ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD)	V_{ESD}	± 15	kV
Contact discharge		± 8	
Peak pulse power (tp=8/20us)	P_{PK}	150	W
Peak pulse current (tp=8/20us)	I_{PP}	5	A
Operation & Storage temperature range	T_J, T_{STG}	-55 ~ +150	°C

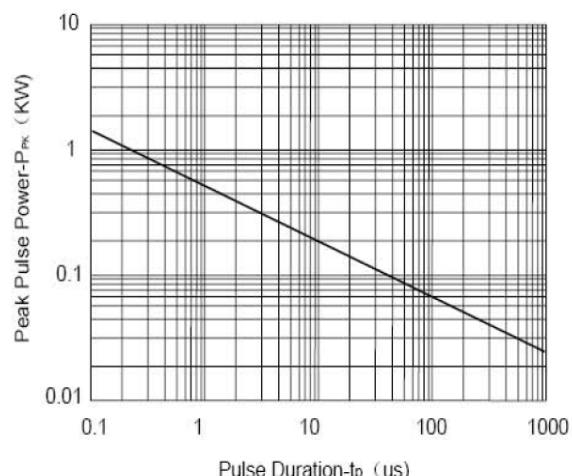
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Reverse Working Voltage	V_{RWM}	I/O-to-GND	-	-	5	V
Reverse Leakage Current	I_R	$V_{RWM}=5\text{V}$, I/O-to-GND	-	-	1	μA
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$, I/O-to-GND	6	-	-	V
Forward Voltage	V_F	$I_T=15\text{mA}$	-	0.85	1.2	V
Clamping Voltage	V_{Clamp}	$I_{PP}=1\text{A}$, $t_p=8/20\text{us}$, I/O-to-GND	-	-	15.5	V
		$I_{PP}=5\text{A}$, $t_p=8/20\text{us}$, I/O-to-GND	-	-	25	
Junction capacitance	C_J	I/O-to-GND $V_R=0$, $f=1\text{MHz}$	-	0.45	0.8	pF
		I/O-to-I/O $V_R=0$, $f=1\text{MHz}$	-	0.3	0.6	pF

RATINGS AND CHARACTERISTICS CURVES

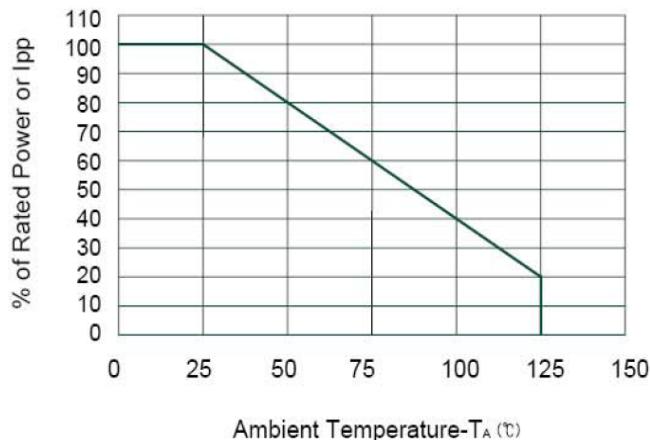


Pulse Waveform

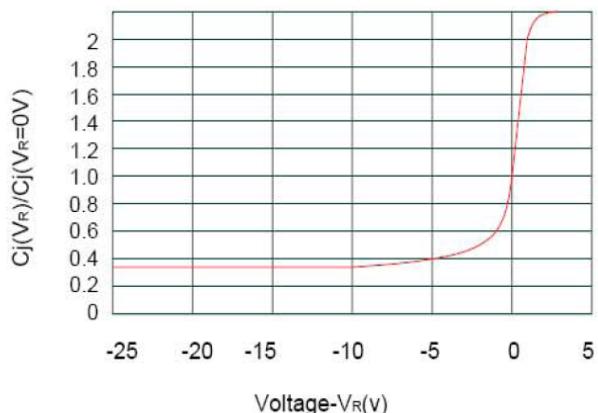


Non-Repetitive Peak Pulse Power vs. Pulse Time

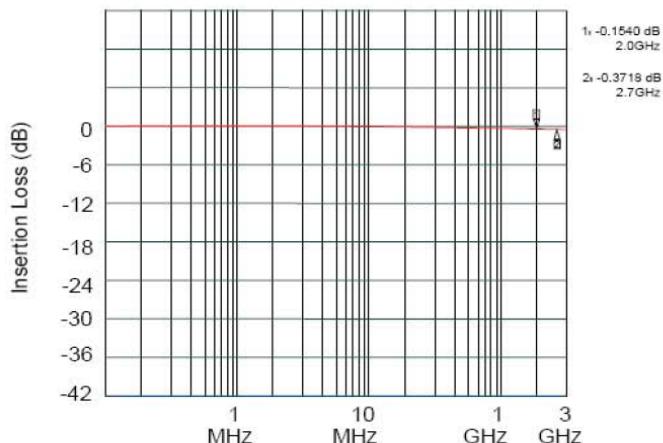
RATINGS AND CHARACTERISTICS CURVES



Power Derating Curve



Junction Capacitance vs. Reverse Voltage



Insertion Loss S21